

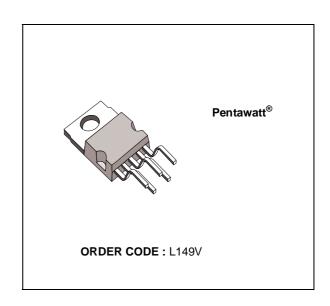
# **4A LINEAR DRIVER**

- HIGH OUTPUT CURRENT (4A peak)
- HIGH CURRENT GAIN (10.000 typ.)
- OPERATION UP TO ± 20 V
- THERMAL PROTECTION
- SHORT CIRCUIT PROTECTION
- OPERATION WITHIN SOA
- HIGH SLEW-RATE (30 V/µs)

#### **DESCRIPTION**

The L149 is a general purpose power booster in Pentawatt ® package consisting of a quasi-complentary darlington output stage with the associated biasing system an inhibit facility.

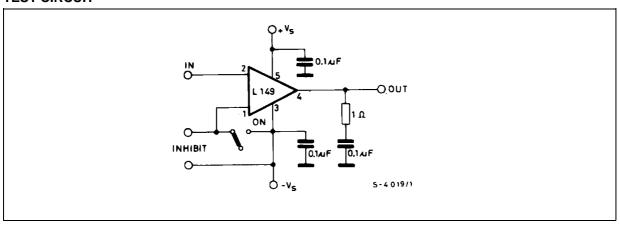
The device is particularly suited for use with an operational amplifier inside a closed loop configuration to increase output current.



### **ABSOLUTE MAXIMUM RATINGS**

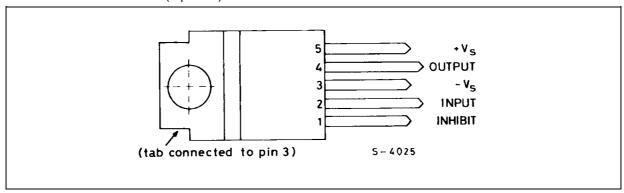
Symbol	Parameter	Value	Unit
Vs	Supply Voltage	±20	V
Vi	Input Voltage		Vs
V <sub>5</sub> - V <sub>4</sub>	Upper Power Transistor VCE	40	V
V <sub>4</sub> - V <sub>3</sub>	Lower Power Transistor V <sub>CE</sub>	40	V
Io	DC Output Current	3	Α
Io	Peak Output Current (internally limited)	4	Α
VINH	Input Inhibit Voltage	- Vs + 5 - Vs - 1.5	V
P <sub>tot</sub>	Total Power Dissipation at T <sub>case</sub> = 75 °C)	25	W

### **TEST CIRCUIT**

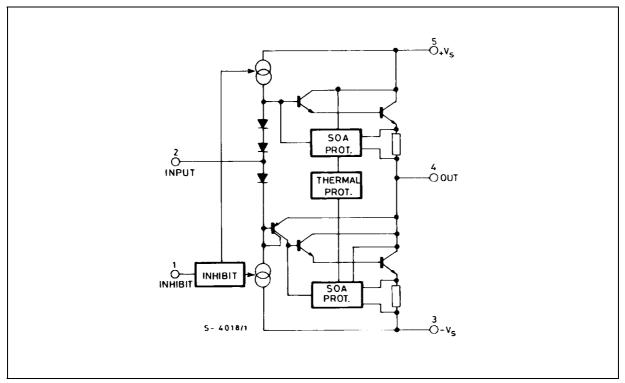


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# **CONNECTION DIAGRAM** (top view)



### **SCHEMATIC DIAGRAM**



### THERMAL DATA

Symbol	Parameter	Value	Unit
Rth-j-case	Thermal resistance junction-case max	3	°C/W

# **ELECTRICAL CHARACTERISTICS** ( $T_j = 25 \, ^{\circ}\text{C}, \ V_s = \pm \, 16\text{V}$ )

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage				± 20	V
I <sub>d</sub>	Quiescent Drain Current	V <sub>s</sub> = ± 16 V		30		mA
l <sub>in</sub>	Input current	$V_s = \pm 16 \text{ V}$ $Vi = 0V$		200	400	μΑ
h <sub>FE</sub>	DC current drain	$V_s = \pm 16 \text{ V}$ Io = 3A	6000	10000		-
Gv	Voltage gain	$V_s = \pm 16 \text{ V}$ Io = 1.5A		1		-
V <sub>CEsat</sub>	Saturation voltage (for each transistor)	Io = 3A			3.5	٧
Vos	Input offset voltage	$V_{s} = \pm 16 \text{ V}$			0.3	V
$V_{INH}$	Inhibit input voltage (pins 1-3)	ON condition			± 0.3	V
		OFF condition	± 1.8			V
R <sub>INH</sub>	Inhibit input resistance			2.0		ΚΩ
SR	Slew rate			30		V/μs
В	Power bandwidth	$V_{o} = \pm 10V, d = 1\%, R_L = 8\Omega$		200		KHz

### **APPLICATION INFORMATION**

Figure 1. High slew-rate power operational amplifier (SR =  $13V/\mu s$ )

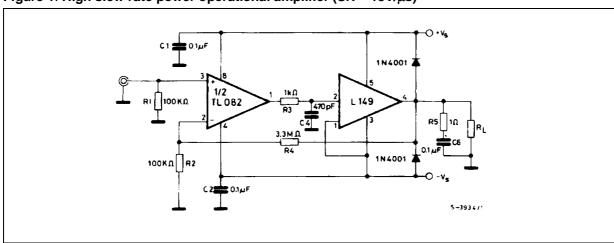


Figure 2. Maximum saturation voltage vs. output current.

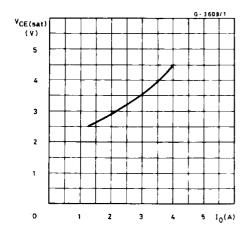


Figure 4: Supply voltage rejection vs. frequency.

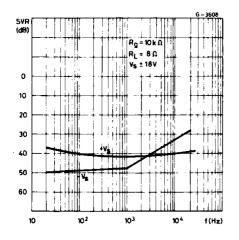


Figure 6. Distorsion vs. output power (f = 1KHz).

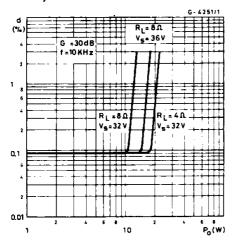


Figure 3. Current limiting characteristics.

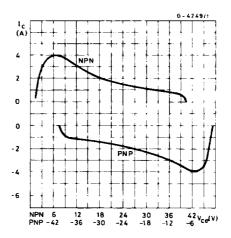


Figure 5: Distorsion vs. output power (f = 1 KHz).

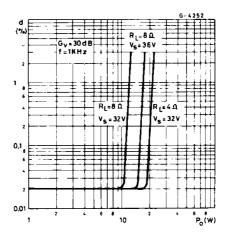
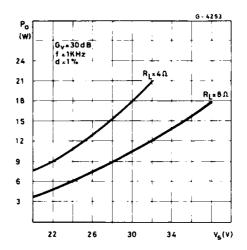
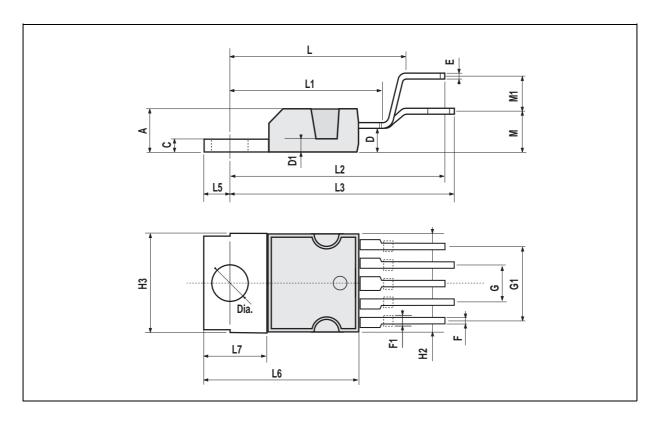


Figure 7. Output power vs. supply voltage.



## PENTAWATT PACKAGE MECHANICAL DATA

DIM.		mm			inch	
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			4.8			0.189
С			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
Е	0.35		0.55	0.014		0.022
F	0.8		1.05	0.031		0.041
F1	1		1.4	0.039		0.055
G		3.4		0.126	0.134	0.142
G1		6.8		0.260	0.268	0.276
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		17.85			0.703	
L1		15.75			0.620	
L2		21.4			0.843	
L3		22.5			0.886	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
М		4.5			0.177	
M1		4			0.157	
Dia	3.65		3.85	0.144		0.152



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